

PAT-NO: JP404196133A
DOCUMENT-IDENTIFIER: JP 04196133 A
TITLE: MANUFACTURE OF SEMICONDUCTOR DEVICE

PUBN-DATE: July 15, 1992

INVENTOR-INFORMATION:

NAME COUNTRY

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APPL-NO: JP02322104

APPL-DATE: November 26, 1990

INT-CL (IPC): H01L021/338 , H01L029/50 , H01L029/812

ABSTRACT:

PURPOSE: To relax the damage in an active region, to realize the high reliability of the title device and to enhance the withstand voltage of the title device by a method wherein a first insulating film whose etching characteristic is different from that of a second insulating film is formed between the second insulating film and the active region.

CONSTITUTION: A first opening part 10 in a second insulating film 4 as an upper layer is formed by an anisotropic etching operation; at this time, a first insulating film 21, as a lower layer, whose etching characteristic is different exists. As a result, the damage by the anisotropic operation to an active region 2 is relaxed. A gate length 11 is controlled by the part 10 in the film 4; a recess width W_2 is controlled by a second opening 22, in the film 21, whose width is wider than that of the part 10. As a result, the distance d_2 between an edge part at a gate electrode 12 and a recess edge part is ensured stably, and a high withstand voltage can be achieved. Especially when a sidewall is used, the withstand voltage can be enhanced while the gate length is being controlled.

